



Fast CMOS 3.3V 8-Bit Latched Transceiver

Product Features

- Compatible with LCXTM and LVTTM families of products
- Supports 5V tolerant mixed signal mode operation
 - Input can be 3V or 5V
 - Output can be 3V or connected to 5V bus
- Advanced low power CMOS operation
- Excellent output drive capability: Balanced drives (24 mA sink and source)
- Low ground bounce outputs
- · Hysteresis on all inputs
- Industrial operating temperature range: -40°C to +85°C
- Packages available:
 - -24-pin 173-mil wide plastic TSSOP(L)
 - -24-pin 150-mil wide plastic QSOP(Q)
 - -24-pin 150-mil wide plastic TQSOP (R)
 - -24-pin 300-mil wide plastic SOIC(S)

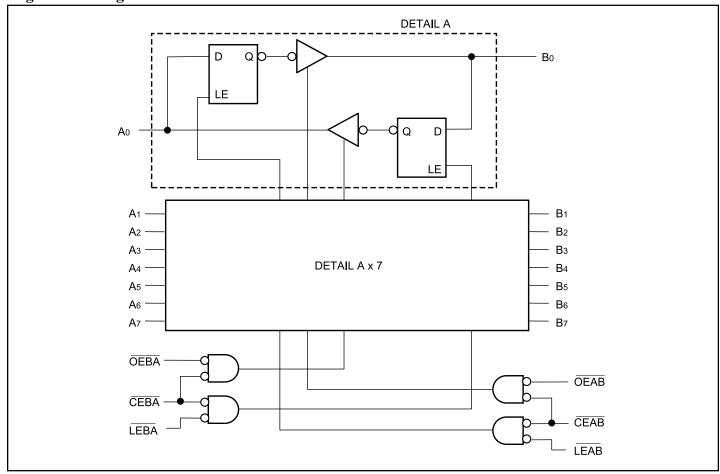
Product Description

Pericom Semiconductor's PI74LPT series of logic circuits are produced in the Company's advanced 0.6 micron CMOS technology, achieving industry leading speed grades.

The PI74LPT543 is an 8-bit wide non-inverting transceiver designed with two sets of eight D-type latches with separate input and output controls for each set. For data flow from A to B, for example, the A-to-B Enable (\overline{CEAB}) input must be LOW in order to enter data from A0–A7 or to take data from B0–B7, as indicated in the Truth Table. With \overline{CEAB} LOW, a LOW signal makes the A-to-B latches transparent; a subsequent LOW-to-HIGH transition of the \overline{LEAB} signal puts the A latches in the storage mode and their outputs no longer change the A inputs. With \overline{CEAB} and \overline{OEAB} both LOW, the 3-state B output buffers are active and reflect the data present at the output of the A latches. Control of data from B to A is similar, but uses the \overline{CEAB} , \overline{LEAB} , and \overline{OEAB} inputs.

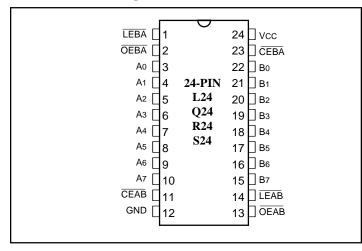
The PI74LPT543 can be driven from either 3.3V or 5.0V devices allowing this device to be used as a translator in a mixed 3.3/5.0V system.

Logic Block Diagram





Product Pin Configuration



Product Pin Description

Pin Name	Description
OEAB	A-to-B Output Enable Input (Active LOW)
ŌEBĀ	B-to-A Output Enable Input (Active LOW)
CEAB	A-to-B Enable Input (Active LOW)
CEBA	B-to-A Enable Input (Active LOW)
LEAB	A-to-B Latch Enable Input (Active LOW)
LEBA	B-to-A Latch Enable Input (Active LOW)
A0-A7	A-to-B Data Inputs or B-to-A 3-State Outputs
B0-B7	B-to-A Data Inputs or A-to-B 3-State Outputs
GND	Ground
Vcc	Power

Truth Table (Non-Inverting)^(1,2) For A-to-B (Symmetric with B-to-A)

Inputs			Latch Status	Output Buffers
CEAB	LEAB	OEAB	A-to-B	B0–B7
Н	X	X	Storing	High-Z
X	Н	X	Storing	X
X	X	Н	X	High Z
L	L	L	Transparent	Current A Inputs
L	Н	L	Storing	Previous* A Inputs

Notes:

1. *Before LEAB LOW-to-HIGH Transition

H = HIGH Voltage Level

L = LOW Voltage Level

X = Don't Care or Irrevelant

2. A-to-B data flow shown; B-to-A flow control is the same, except using CEBA, LEBA, and OEBA.



Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature
Ambient Temperature with Power Applied—40°C to +85°C
Supply Voltage to Ground Potential (Inputs & Vcc Only)0.5V to +7.0V
Supply Voltage to Ground Potential (Outputs & D/O Only)0.5V to +7.0V
DC Input Voltage0.5V to +7.0V
DC Output Current
Power Dissipation

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

DC Electrical Characteristics (Over the Operating Range, $TA = -40^{\circ}C$ to $+85^{\circ}C$, VCC = 2.7V to 3.6V)

Parameters	Description	Test Conditions(1)		Min.	Typ ⁽²⁾	Max.	Units
VIH	Input HIGH Voltage (Input pins)	Guaranteed Logic HIGH Level		2.2		5.5	V
	Input HIGH Voltage (I/O pins)			2.0	_	5.5	V
VIL	Input LOW Voltage (Input and I/O pins)	Guaranteed Logic LOW L	evel	-0.5	_	0.8	V
Іїн	Input HIGH Current (Input pins)	Vcc = Max.	$V_{IN} = 5.5V$	_		±1	μA
	Input HIGH Current (I/O pins)	$V_{CC} = Max.$	$V_{IN} = V_{CC}$	_	_	±1	μA
IIL	Input LOW Current (Input pins)	Vcc = Max.	Vin = GND	_	_	±1	μA
	Input LOW Current (I/O pins)	$V_{CC} = Max.$	$V_{IN} = GND$	_	_	±1	μA
Iоzн	High Impedance Output Current	$V_{CC} = Max.$ $V_{OUT} = 5.5V$		_	_	±1	μΑ
Iozl	(3-State Output pins)	$V_{CC} = Max.$ $V_{OUT} = GND$		_	_	±1	μΑ
Vik	Clamp Diode Voltage	$V_{CC} = Min., I_{IN} = -18 \text{ mA}$	_	-0.7	-1.2	V	
Іорн	Output HIGH Current	$V_{CC} = 3.3V$, $V_{IN} = V_{IH}$ or $V_{IN} = V_{IH}$	-36	-60	-110	mA	
Iodl	Output LOW Current	$V_{CC} = 3.3V$, $V_{IN} = V_{IH}$ or $V_{IN} = V_{IH}$	50	90	200	mA	
Vон	Output HIGH Voltage	Vcc = Min.	$V_{CC} = Min.$ $I_{OH} = -0.1 \text{ mA}$		_	_	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -3 \text{ mA}$		2.4	3.0	_	V
		Vcc = 3.0V,	Iон = $-8 mA$	2.4(5)	3.0	_	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$	Iон = $-24 mA$	2.0	_	_	
Vol	Output LOW Voltage	Vcc = Min.	IoL = 0.1 mA	_	_	0.2	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$	IoL = 16 mA	_	0.2	0.4	V
			IoL = 24 mA	_	0.3	0.5	V
Ios	Short Circuit Current ⁽⁴⁾	$V_{CC} = Max.^{(3)}, V_{OUT} = GN$	-60	-85	-240	mA	
Ioff	Power Down Disable	$V_{CC} = 0V$, V_{IN} or $V_{OUT} \le$	_		±100	μΑ	
VH	Input Hysteresis		_	150	_	mV	

Notes:

- 1. For Max. or Min. conditions, use appropriate value specified under Electrical Characteristics for the applicable device type.
- 2. Typical values are at Vcc = 3.3V, $+25^{\circ}\hat{C}$ ambient and maximum loading.
- 3. Not more than one output should be shorted at one time. Duration of the test should not exceed one second.
- 4. This parameter is guaranteed but not tested.
- 5. VoH = Vcc 0.6V at rated current.

Capacitance ($TA = 25^{\circ}C$, f = 1 MHz)

Parameters ⁽¹⁾	Description	Test Conditions	Тур.	Max.	Units
Cin	Input Capacitance	$V_{IN} = 0V$	4.5	6	pF
Соит	Output Capacitance	$V_{OUT} = 0V$	5.5	8	pF

Note:

1. This parameter is determined by device characterization but is not production tested.



Power Supply Characteristics

Parameters	Description	Test Conditions ⁽¹⁾			Typ ⁽²⁾	Max.	Units
Icc	Quiescent Power Supply Current	Vcc = Max.	VIN = GND or VCC		0.1	10	μΑ
ΔΙcc	Quiescent Power Supply Current TTL Inputs HIGH	Vcc = Max.	$V_{\text{IN}} = V_{\text{CC}} - 0.6V^{(3)}$		2.0	30	μΑ
Iccd	Dynamic Power Supply ⁽⁴⁾	Vcc = Max., Outputs Open CEAB and OEAB = GND CEBA = Vcc One Bit Toggling 50% Duty Cycle	Vin = Vcc Vin = GND		50	75	μA/ MHz
Ic	Total Power Supply Current ⁽⁶⁾	Vcc = Max., Outputs Open fi = 10 MHz 50% Duty Cycle CEAB and OEAB = GND CEBA = Vcc One Bit Toggling	Vin = Vcc - 0.6V Vin = GND		0.6	2.3	mA
		Vcc = Max., Outputs Open fi = 2.5 MHz 50% Duty Cycle CEAB and OEAB = GND CEBA = Vcc 8 Bits Toggling	Vin = Vcc - 0.6V Vin = GND		2.1	4.7 ⁽⁵⁾	

Notes:

1. For Max. or Min. conditions, use appropriate value specified under Electrical Characteristics for the applicable device.

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- 2. Typical values are at Vcc = 3.3V, +25°C ambient.
- 3. Per TTL driven input; all other inputs at Vcc or GND.
- 4. This parameter is not directly testable, but is derived for use in Total Power Supply Calculations.
- 5. Values for these conditions are examples of the Icc formula. These limits are guaranteed but not tested.
- 6. Ic =Iquiescent + Inputs + Idynamic
 - $IC = ICC + \Delta ICC DHNT + ICCD (fCP/2 + fiNi)$
 - Icc = Quiescent Current (Iccl, Icch and Iccz)
 - Δ Icc = Power Supply Current for a TTL High Input
 - DH = Duty Cycle for TTL Inputs High
 - $N_T = Number of TTL Inputs at DH$
 - ICCD = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)
 - fcp = Clock Frequency for Register Devices (Zero for Non-Register Devices)
 - NCP = Number of Clock Inputs at fCP
 - fi = Input Frequency
 - $N_I = Number of Inputs at fi$
 - All currents are in milliamps and all frequencies are in megahertz.



Switching Characteristics over Operating Range⁽¹⁾

			LPT543		LPT543A		LPT543C		
			Com.		Com.		Com.		
Parameters	Description	$\boldsymbol{Conditions}^{(2)}$	Min.(3)	Max.	Min.(3)	Max.	Min.(3)	Max.	Units
tplh	Propagation Delay Transparent	CL = 50 pF	2.5	8.5	2.5	6.5	2.5	5.3	ns
tphl	Mode An to Bn or Bn to An	$R_L = 500\Omega$							
tplh	Propagation Delay		2.5	12.5	2.5	8.0	2.5	7.0	ns
tPHL	$\overline{\text{LEBA}}$ to An, $\overline{\text{LEAB}}$ to Bn								
tpzh	Output Enable Time		2.0	12.0	2.0	9.0	2.0	8.0	ns
tpzl	OEBA or OEAB to An or Bn								
	CEBA or CEAB to An or Bn								
tpzh	Output Disable Time(3)		2.0	9.0	2.0	7.5	2.0	6.5	ns
tpzl	OEBA or OEAB to An or Bn								
	CEBA or CEAB to An or Bn								
tsu	Setup Time, HIGH or LOW		3.0	_	2.0	_	2.0	_	ns
	An or Bn to $\overline{\text{LEBA}}$ or $\overline{\text{LEAB}}$								
tH	Hold Time, HIGH or LOW		2.0	_	2.0	_	2.0	_	ns
	An or Bn to $\overline{\text{LEBA}}$ or $\overline{\text{LEAB}}$								
tw	LEBA or LEAB Pulse Width LOW(3)		5.0	-	5.0	_	5.0	_	ns

Notes:

- 1. Propagation Delays and Enable/Disable times are with $Vcc = 3.3V \pm 0.3V$, normal range. For Vcc = 2.7V, extended range, all Propagation Delays and Enable/Disable times should be degraded by 20%.
- 2. See test circuit and wave forms.
- 3. Minimum limits are guaranteed but not tested on Propagation Delays.
- 4. This parameter is guaranteed but not production tested.
- 5. Skew between any two outputs, of the same package, switching in the same direction. This parameter is guaranteed by design.